

REMARKS

RESTRICTION REQUIREMENT

The Examiner requests that an election be made as to the claims.

With respect to election of claims, the Applicant elects without traverse (and without prejudice towards non-elected claims) claims 20, 24-26 and 30, which were designated as Invention I by the Office. There are no new claims added in this response. In addition, claim 29 was not addressed by the Examiner; however, the Applicant considers this claim to fall under Independent claim 27, and therefore, should have been included under the Invention II heading by the Examiner. Clarification is requested by the Applicant in the next Office Action.

Respectfully submitted,

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LISTING OF THE CURRENT CLAIMS

IN ACCORDANCE WITH REVISED AMENDMENT PRACTICE

Claims 1-11: Previously Withdrawn

Claims 12-19: Canceled.

Claim 20: (Original) A method of removing a spin-on compound, comprising:
spin-depositing a spin-on compound on a surface of a substrate, wherein the spin-on compound comprises silicon, wherein the first solvent comprises propyl acetate, and wherein the second solvent comprises ethyl lactate; and
spin-rinsing the spin-on compound with a solvent mixture, wherein the solvent mixture comprises a first solvent that dissolves the spin-on compound, and a second solvent that is inert to the spin-on compound.

Claims 21-23: Previously Canceled.

Claim 24: (Previously Added) The method of claim 20, wherein the substrate comprises a trench.

Claim 25: (Previously Added) The method of claim 24, wherein the spin-on compound is spin-deposited into the trench.

Claim 26: (Previously Added) The method of claim 20, wherein the spin-on compound is partially removed.

Claim 27: (Canceled) A method of forming a shallow trench isolation structure, comprising:
partially removing the spin-on compound according to the method of claim 20 such that an upper surface of the remaining compound is below the surface of the substrate;

depositing a second compound onto the substrate surface and onto the upper surface of the remaining spin-on compound by chemical vapor deposition.

Claim 28: (Canceled) The method of claim 27, further comprising planarizing the isolation structure such that the surface of the substrate and an upper surface of the second compound are substantially coplanar.

Claim 29: (Canceled) The method of claim 27, wherein the substrate surface and the trench further comprise a thermal oxide coat.

Claim 30: (Amended) The method of claim 20 ~~one of claims 20 or 27~~, wherein the spin-on compound is formed from at least one compound selected from the group consisting of methylsilsesquioxane, hydrogensilsesquioxane, methylhydridosilsesquioxane, silicate, and perhydrosilazane.

Claim 31: (Canceled) The method of claim 27, wherein the second compound is formed from tetraethylorthosilicate or silane.